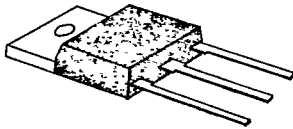


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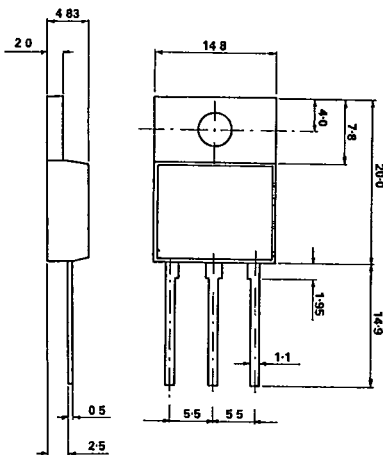
**BUW 51**

## NPN MULTI-EPITAXIAL POWER TRANSISTOR

Suitable for high current, high speed,  
low voltage applications

### MECHANICAL DATA

Dimensions in mm



### FEATURES

- LOW  $V_{CE(SAT)}$
- FAST SWITCHING
- HIGH CURRENT
- HIGH RELIABILITY

### APPLICATIONS

- HIGH FREQUENCY AND EFFICIENCY CONVERTERS
- SWITCHING REGULATORS
- MOTOR CONTROLS

SOT93

(ALSO AVAILABLE IN CHIP FORM)

### ABSOLUTE MAXIMUM RATINGS ( $T_{CASE} = 25^{\circ}\text{C}$ unless otherwise stated)

$V_{CEX}$	Collector-emitter voltage ( $V_{BE} = -1.5\text{V}$ )	300V
$V_{CEO}$	Collector-emitter voltage ( $I_B = 0$ )	200V
$V_{EBO}$	Emitter-base voltage	7V
$I_C$	Collector current	20A
$I_{C(PK)}$	Peak collector current	28A
$I_B$	Base current	4A
$I_{B(PK)}$	Peak base current	7A
$P_{tot}$	Total dissipation at $T_{CASE} = 25^{\circ}\text{C}$	150W
$T_{stg}$	Storage temperature	-55 to $200^{\circ}\text{C}$
$T_J$	Maximum operating junction temperature	$200^{\circ}\text{C}$
$R_{th}$	Thermal resistance (junction-case)	Max. $1.0^{\circ}\text{C/W}$

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**ELECTRICAL CHARACTERISTICS** ( $T_{CASE} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE0(sus)}$ Collector-emitter sustaining voltage	$I_B = 0, I_C = 0.2A$ $L = 25mH$	200			V
$V_{(BR)EBO}$ Emitter base breakdown voltage	$I_C = 0$ $I_E = 50mA$	7			V
$I_{CEX}$ Collector cut-off current	$V_{BE} = -1.5V$ $V_{CE} = V_{CEX}$ $T_J = 100^{\circ}C$			0.5 2.0	mA mA
$I_{CER}$ Collector cut-off current	$R_{BE} = 10\Omega$ $V_{CE} = V_{CEX}$ $T_J = 100^{\circ}C$			0.5 2.5	mA mA
$I_{EBO}$ Emitter cut-off current	$I_C = 0$ $V_{BE} = -5V$			1.0	mA
$V_{CE(sat)*}$ Collector-emitter saturation voltage	$I_C = 10A$ $I_B = 1A$ $T_J = 100^{\circ}C$		0.45	0.9	V
			0.6	1.5	V
		$I_C = 5A$ $I_B = 0.25A$ $T_J = 100^{\circ}C$	0.4	0.8	V
$V_{BE(sat)*}$ Emitter-base saturation voltage	$I_C = 10A$ $I_B = 1A$ $T_J = 100^{\circ}C$		1.1	1.4	V
			1.0	1.4	V

**SWITCHING CHARACTERISTICS** ( $T_{CASE} = 25^{\circ}C$  unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
<b>SWITCHING TIMES ON RESISTIVE LOAD</b>					
$t_r$ Rise time	$I_C = 14A$ $V_{CC} = 160V$ $V_{BB} = -5V$ $R_{B2} = 1.4\Omega$ $t_p = 30\mu s$ $I_{B1} = 1.7A$	0.3	0.6		$\mu s$
$t_s$ Storage time		0.6	1.4		$\mu s$
$t_f$ Fall time		0.12	0.3		$\mu s$
<b>TURN-ON SWITCHING CHARACTERISTICS</b>					
$di_c/dt$ On state collector current current rate of rise	$R_C = 0$ $V_{CC} = 160V$ $I_{B1} = 1.5A$ $T_J = 100^{\circ}C$	35 30	75 65		$A/\mu s$ $A/\mu s$
$V_{CE}(2\mu s)$ Collector-emitter voltage after applied base drive	$V_{CC} = 160V$ $R_C = 16\Omega$ $I_{B1} = 1A$ $T_J = 100^{\circ}C$	1.8	3.0		V
$V_{CE}(4\mu s)$		3.0	5.0		V
		1.1	1.7		V
		1.4	2.5		V
<b>TURN-OFF SWITCHING CHARACTERISTICS - INDUCTIVE LOAD, WITH NEGATIVE BIAS</b>					
$t_{si}$ Carrier storage time	$I_C = 10A$ $V_{clamp} = 200V$ $T_J = 100^{\circ}C$ $I_B = 1A$ $L_C = 0.8mH$ $V_{CC} = 160V$ $R_{B2} = 2.5\Omega$ $T_J = 100^{\circ}C$ $V_{BB} = -5V$ $T_J = 100^{\circ}C$	0.7	1.5		$\mu s$
		1.1	2.0		$\mu s$
$t_{fi}$ Fall time		0.06	0.2		$\mu s$
		0.12	0.3		$\mu s$
$t_c$ $V_{CE}/I_C$ Crossover time		0.13	0.3		$\mu s$
		0.24	0.5		$\mu s$
<b>TURN-OFF SWITCHING CHARACTERISTICS - INDUCTIVE LOAD, WITHOUT NEGATIVE BIAS</b>					
$t_{si}$ Carrier storage time	$I_C = 10A$ $V_{clamp} = 200V$ $T_J = 100^{\circ}C$ $I_B = 1A$ $L_C = 0.8mH$	1.5			$\mu s$
		2.7			$\mu s$
$t_{fi}$ Fall time	$V_{CC} = 160V$ $R_{B2} = 4.7\Omega$ $V_{BB} = 0V$ $T_J = 100^{\circ}C$	0.5			$\mu s$
		0.85			$\mu s$

\* Pulse test  $t_p = 300\mu s$   $\delta \leq 2\%$ 

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